NPN Epitaxial Planar Silicon Transistor

2SC3068



# High h<sub>FE</sub>, Low-Frequency General-Purpose Amplifier Applications

### **Applications**

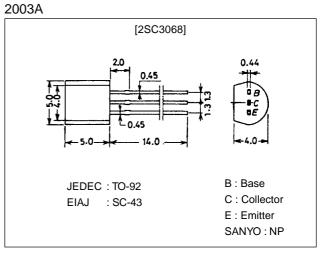
· Low-frequency, general-purpose amplifier., various drivers, muting circuit.

### Features

- $\cdot$  High DC current gain (h\_{FE}=800 to 3200).
- · Large current capacity.
- $\cdot$  Low collector-to-emitter saturation voltage (V<sub>CE(sat)</sub>=0.5V max).
- · High  $V_{EBO}$  ( $V_{EBO} \ge 15V$ ).

## **Package Dimensions**

unit:mm



# **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Sşmbo	Condition	Rating	Uni
Collector-to-Base Voltage	СВО		30	
Collector-to-Emitter Voltage	CEO		25⁄	
Elmitter-to-Base Voltage	EBO		15⁄	
Collector Current	С		300	m
Collector Current (Pulse)	CP		5100	m
Base Current	В		6 <b>A</b>	m
Cellector Dissipation	С		600	m
Jjunction Temperature	Т		150	°C
Storage Temperature	Tst		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

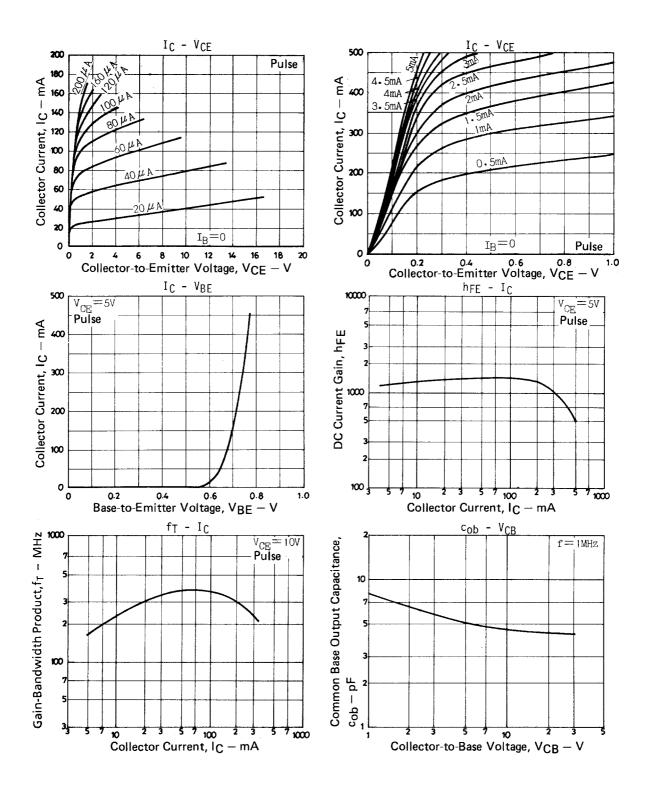
Parameter	Sşmbo	Condition	Ratings			Unit
			mipn	tyc	ma	
Cbllector Cutoff Current	СВО	V <sub>CB</sub> =20V, I <sub>E</sub> =0			0A	μ
Emitter Cutoff Current	EBO	V <sub>EB</sub> =10V, I <sub>C</sub> =0			0A	μ
DC Current Gain	h <sub>FE</sub> 1V	CE=5V, IC=10mA	8 <b>0</b> 0	1 <b>6</b> 0	320	
	h <sub>FE</sub> 2V	CE=5V, IC=200mA	600			
Gain-Bandwidth Product	Т	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA		250		MH
O@tput Capacitance	ob	V <sub>CB</sub> =10V, f=1MHz		4F5		р

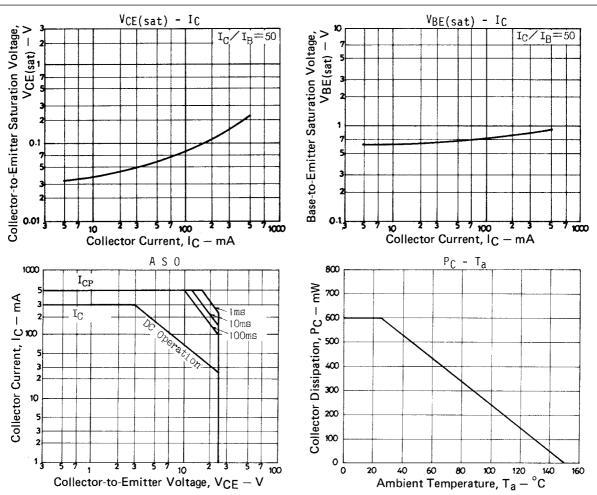
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Parameter	Symbol	Conditions	Ratings			Unit
			mjøn	tyx	ma	Onit
Collector-to-Emitter Saturation Voltage	CE(sat)	I <sub>C</sub> =200mA, I <sub>B</sub> =4mA		0512	0.V	
Base-to-Emitter Saturation Voltage	BE(sat)	I <sub>C</sub> =200mA, I <sub>B</sub> =4mA		0285	1.V	
Collector-to-Base Breakdown Voltage	(BR)CBO	I <sub>C</sub> =10μA, I <sub>E</sub> =0	3V			
Collector-to-Emitter Breakdown Voltage	(BR)CEO	I <sub>C</sub> =1mA, R <sub>BE</sub> =∞	25⁄			
Ethitter-to-Base Breakdown Voltage	(BR)EBO	I <sub>E</sub> =10μΑ, I <sub>C</sub> =θ	1V			





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